

## Product Summary

Device	BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C (Notes 5 & 7)
Q1	30V	32mΩ @ V <sub>GS</sub> = 10V	8.1A
		46mΩ @ V <sub>GS</sub> = 4.5V	6.1A
Q2	-30V	39mΩ @ V <sub>GS</sub> = -10V	-7A
		53mΩ @ V <sub>GS</sub> = -4.5V	-5.6A

## Description

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Power Management Functions
- Analog Switch
- Load Switch

## Features

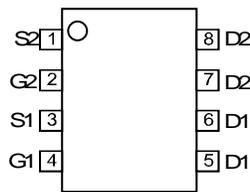
- Low On-Resistance
- N-Channel: 32mΩ @ 10V  
46mΩ @ 4.5V
- P-Channel: 39mΩ @ -10V  
53mΩ @ -4.5V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208<sup>③</sup>
- Marking Information (See Page 2)
- Ordering Information
- Weight: 0.072 grams (Approximate)

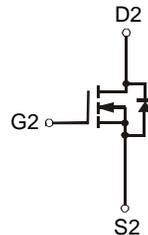


Top View

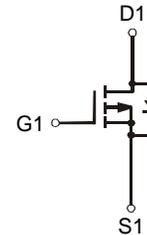


Top View

SO-8



N-Channel MOSFET

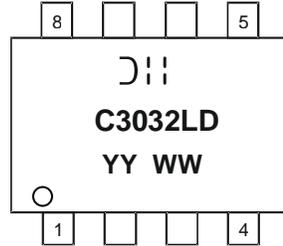


P-Channel MOSFET

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMC3032LSD-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**


Dii = Manufacturer's Marking  
 C3032LD = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 18 = 2018)  
 WW = Week (01 to 53)

**Maximum Ratings N-CHANNEL – Q1** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	8.1	A
		T <sub>A</sub> = +85°C		5.1	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	25	A

**Maximum Ratings P-CHANNEL – Q2** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-7.0	A
		T <sub>A</sub> = +85°C		-4.5	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-25	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	50	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.  
 6. Repetitive rating, pulse width limited by junction temperature.

**Electrical Characteristics N-CHANNEL – Q1** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.45	2.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	23	32	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7A
			32	46		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.6A
Forward Transfer Admittance	Y <sub>fs</sub>	—	7.6	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 7A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	0.7	1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	404.5	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	51.8	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	45.1	—	pF	
Gate Resistance	R <sub>g</sub>	—	1.5	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (10V)	Q <sub>g</sub>	—	9.2	—	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 5.8A
Gate-Source Charge	Q <sub>gs</sub>	—	1.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.8	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.4	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, R <sub>G</sub> = 3Ω, R <sub>L</sub> = 2.6Ω
Turn-On Rise Time	t <sub>r</sub>	—	6.18	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	13.92	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	2.84	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to production testing.

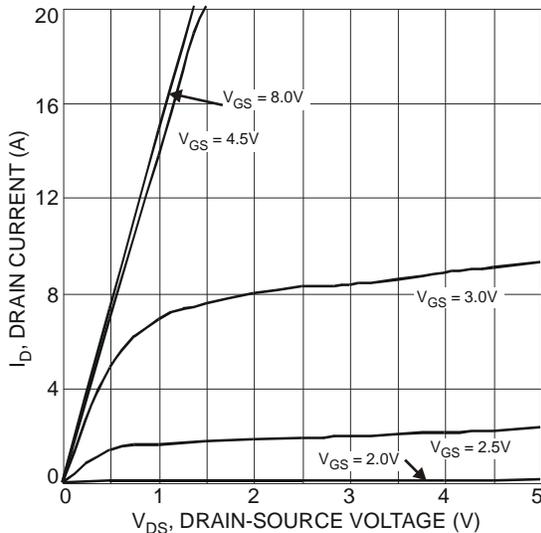


Fig. 1 Typical Output Characteristics

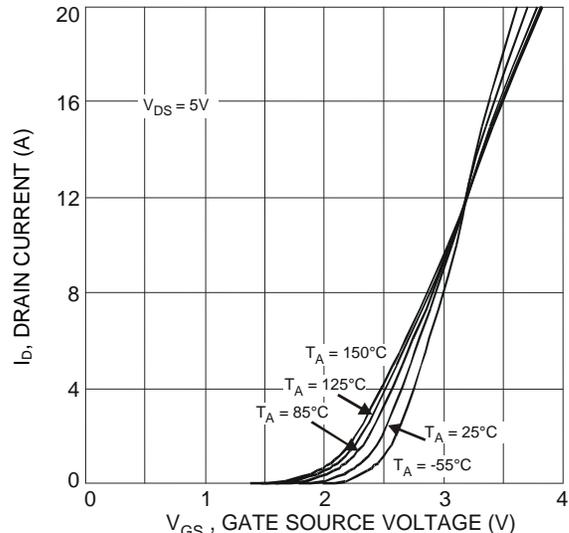


Fig. 2 Typical Transfer Characteristics

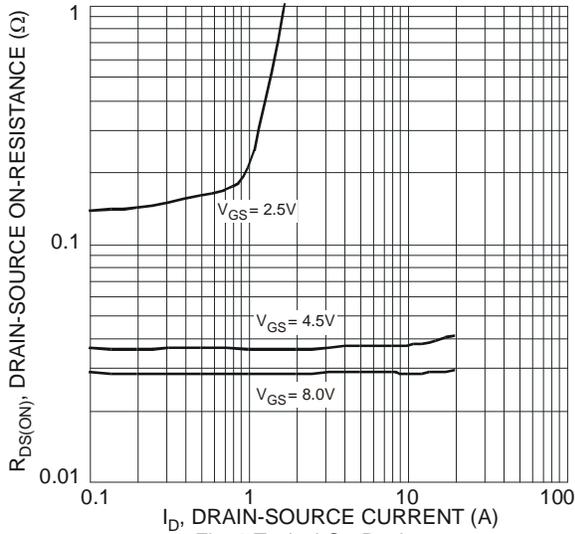


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

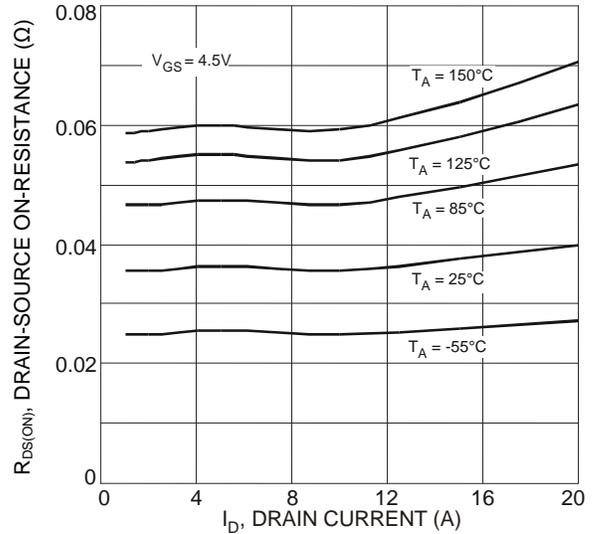


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

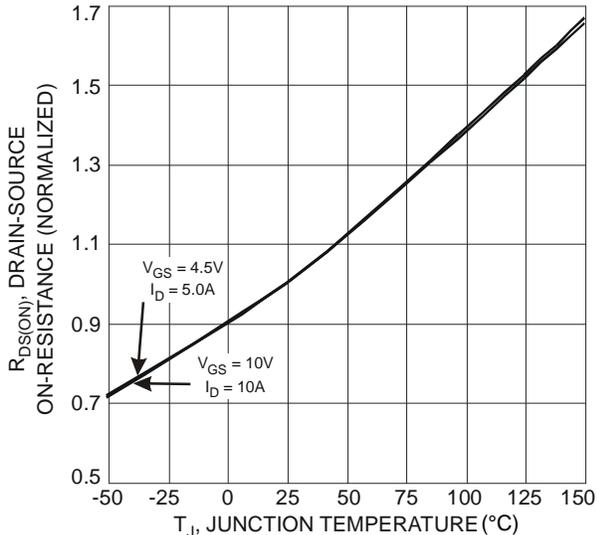


Fig. 5 On-Resistance Variation with Temperature

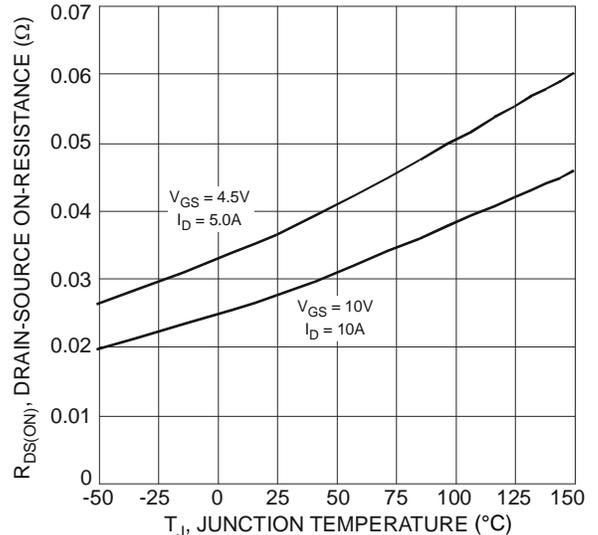


Fig. 6 On-Resistance Variation with Temperature

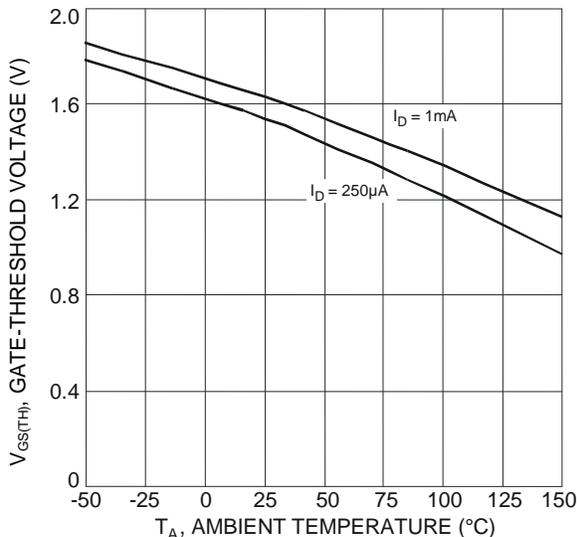


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

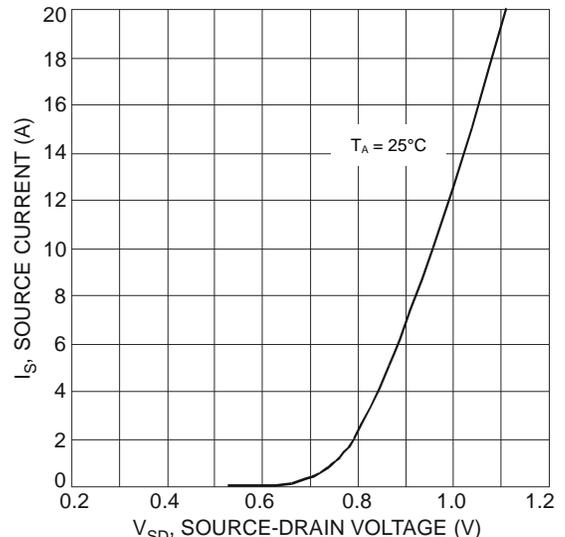
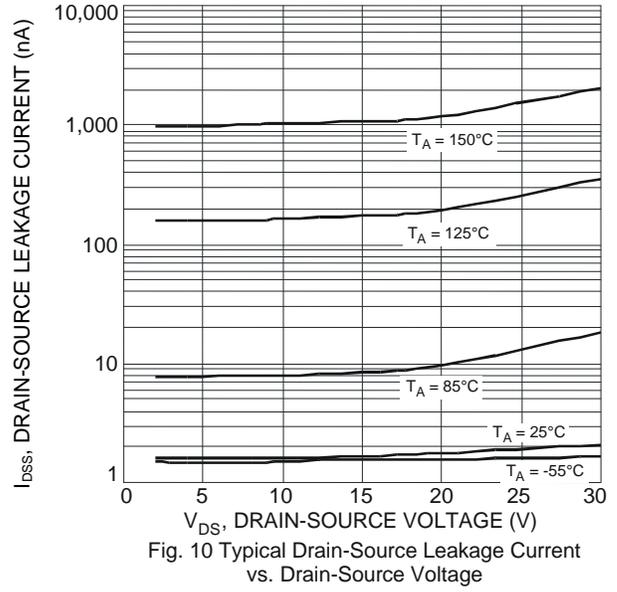
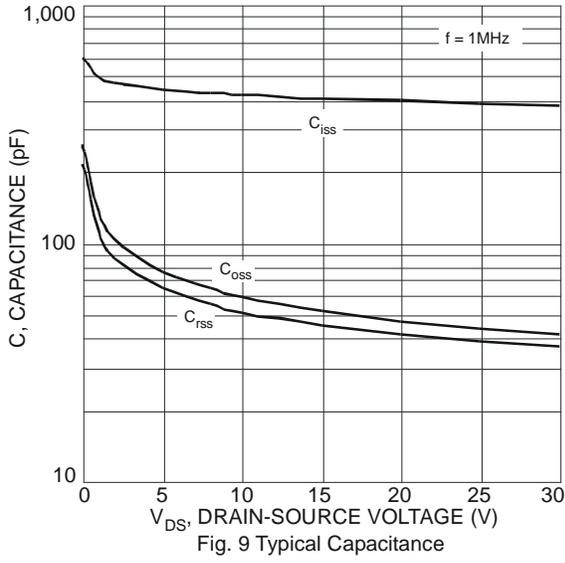


Fig. 8 Diode Forward Voltage vs. Current



**Electrical Characteristics P-CHANNEL** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1	-1.7	-2.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	30	39	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.3A V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.7A
			42	53		
Forward Transfer Admittance	Y <sub>fs</sub>	—	7	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4.3A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	-0.75	-1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.7A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iSS</sub>	—	1002	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oSS</sub>	—	125	—	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	118	—	pF	
Gate Resistance	R <sub>g</sub>	—	13	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (-4.5V)	Q <sub>g</sub>	—	10.1	—	nC	V <sub>GS</sub> = -4.5V/-10V, V <sub>DS</sub> = -15V, I <sub>D</sub> = -6A
Total Gate Charge (-10V)	Q <sub>g</sub>	—	21.1	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	2.8	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	3.2	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	10.1	—	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>R</sub>	—	6.5	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	50.1	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	22.2	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to production testing.

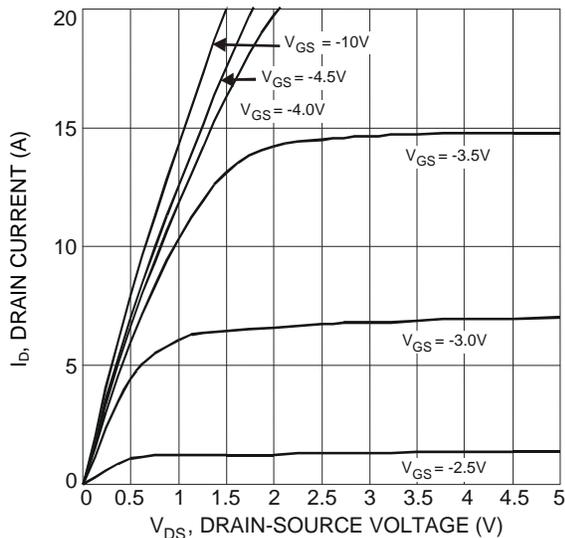


Fig. 11 Typical Output Characteristics

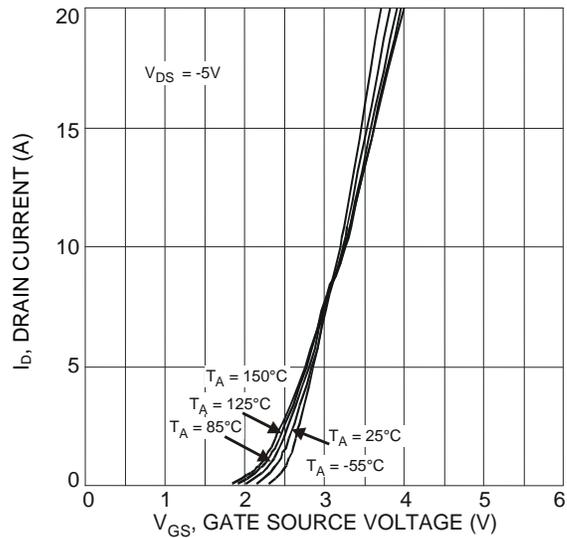


Fig. 12 Typical Transfer Characteristics

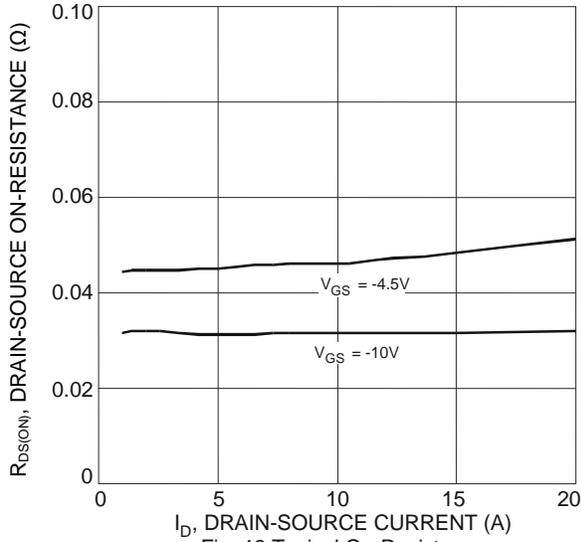


Fig. 13 Typical On-Resistance vs. Drain Current and Gate Voltage

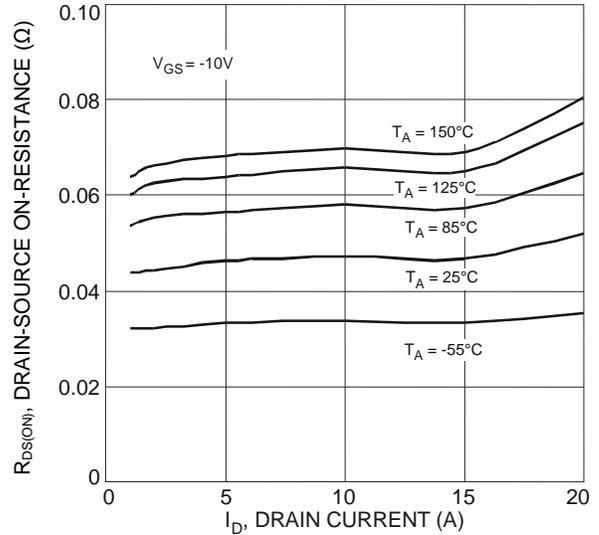


Fig. 14 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

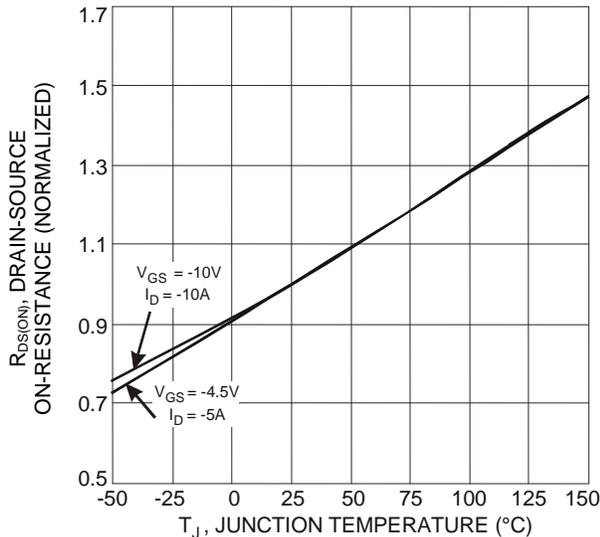


Fig. 15 On-Resistance Variation with Temperature

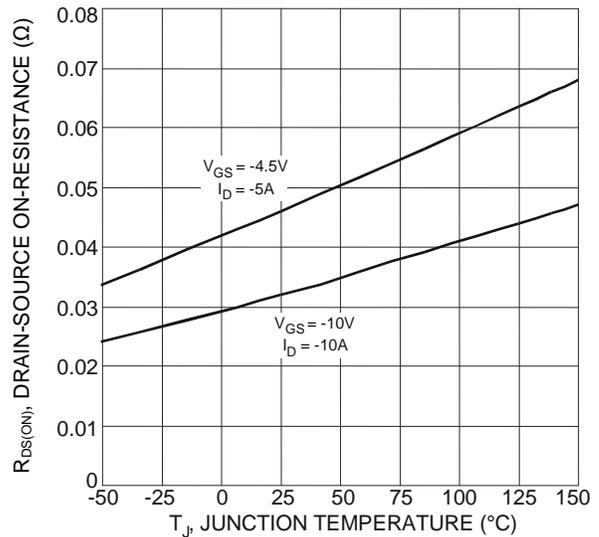


Fig. 16 On-Resistance Variation with Temperature

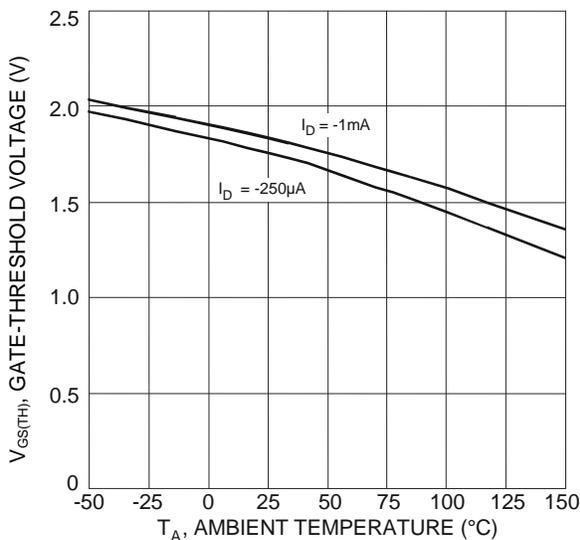


Fig. 17 Gate Threshold Variation vs. Ambient Temperature

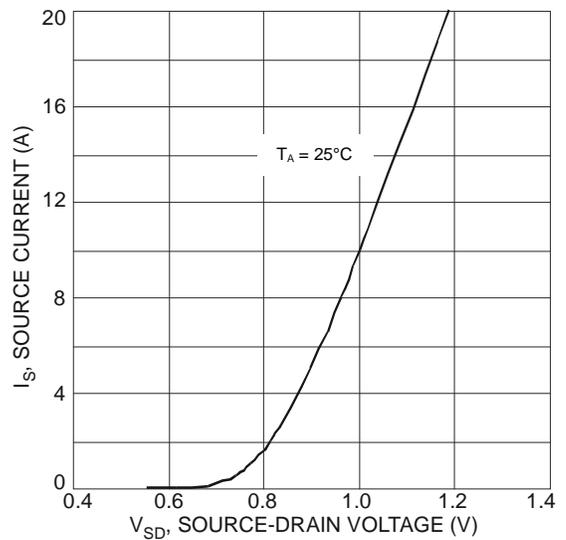
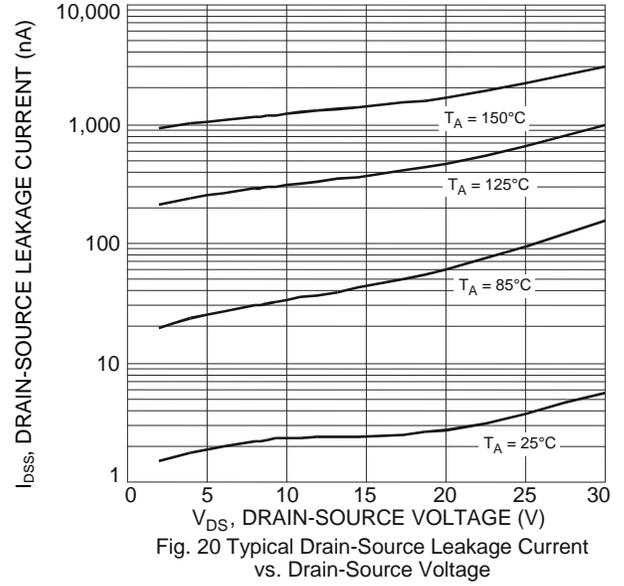
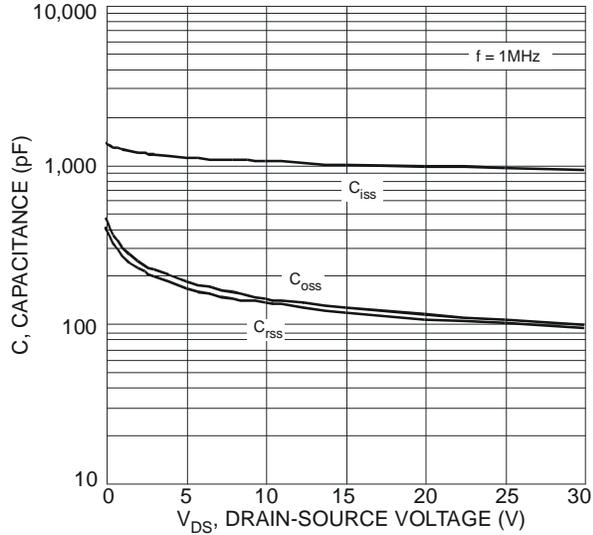


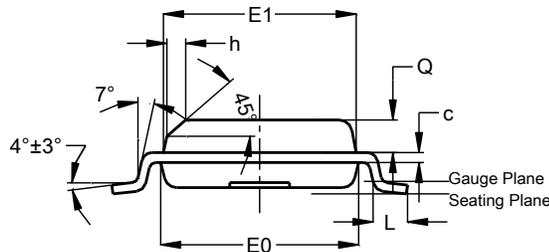
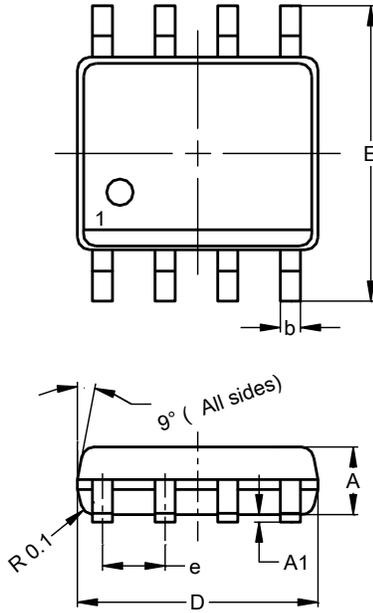
Fig. 18 Diode Forward Voltage vs. Current



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**

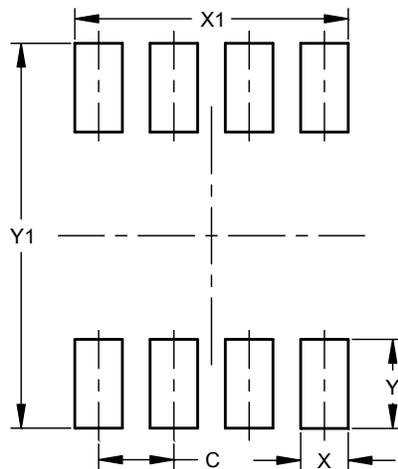


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

NEW PRODUCT

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